

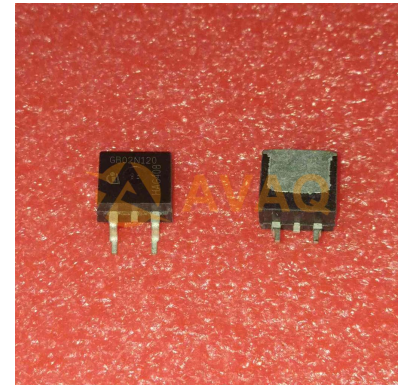
Trans IGBT Chip N-CH 1200V 6.2A 62mW 3-Pin(2+Tab) D2PAK T/R

Manufacturer: [Infineon Technologies Corporation](#)

Package/Case: TO-263

Product Type: Thyristors

Lifecycle: LTB



Images are for reference only

[Inquiry](#)

General Description

SGB02N120 is a power MOSFET transistor, which is designed for high-voltage, high-speed power switching applications. It is manufactured by Infineon Technologies and is part of their CoolMOS™ product family.

Key Features

Drain-source voltage (VDS) of 1200V

Continuous drain current (ID) of 2A

Low on-state resistance (RDS(on)) of 2.2 ohms

Fast switching speed with low gate charge (Qg)

High avalanche ruggedness and robustness

Application

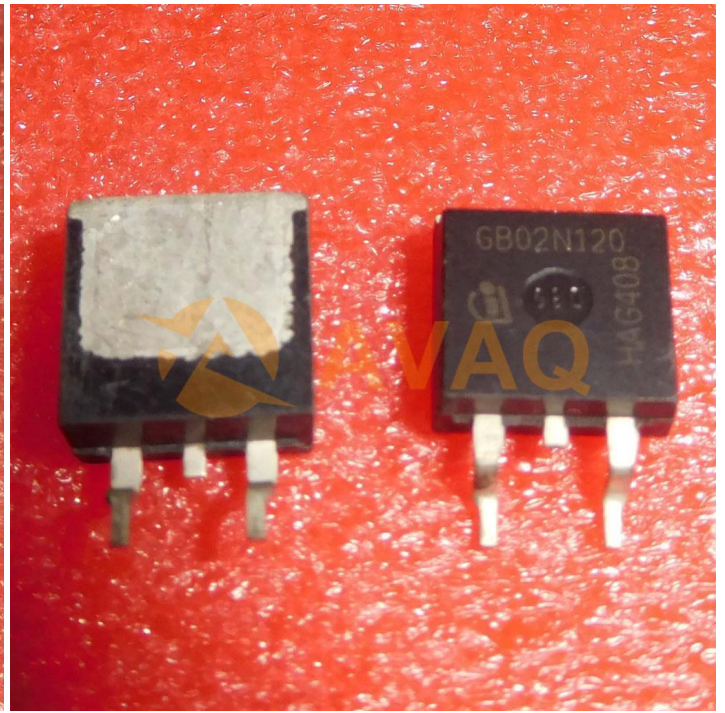
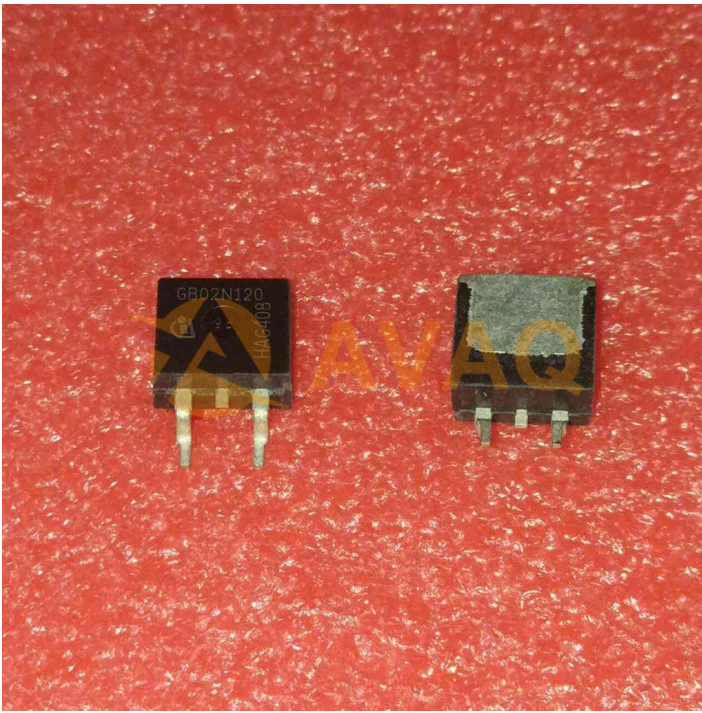
Switching power supplies

High-frequency inverters

DC-DC converters

Motor drives

Lighting ballasts



Recommended For You

SGW30N60HS

Infineon Technologies Corporation

TO-247

SGW50N60HS

Infineon Technologies Corporation

TO-247

SGW30N60

Infineon Technologies Corporation

TO-247

SGP30N60

Infineon Technologies Corporation

PG-TO220-3

SGB10N60A

Infineon Technologies Corporation

TO-263

SGD02N120

Infineon Technologies Corporation

TO-252

SGW25N120

Infineon Technologies Corporation

TO-247

SGW15N120

Infineon Technologies Corporation

TO-247

SGP07N120

Infineon Technologies Corporation

TO-220

SGP20N60

Infineon Technologies Corporation

TO-220

SGB30N60

Infineon Technologies Corporation

TO-263

SGP10N60A

Infineon Technologies Corporation

PG-TO220-3

SGW15N60FKSA1

Infineon Technologies Corporation

BGA

SGB20N60ATMA1

Infineon Technologies Corporation

BGA

SGP30N60XKSA1

Infineon Technologies Corporation

BGA